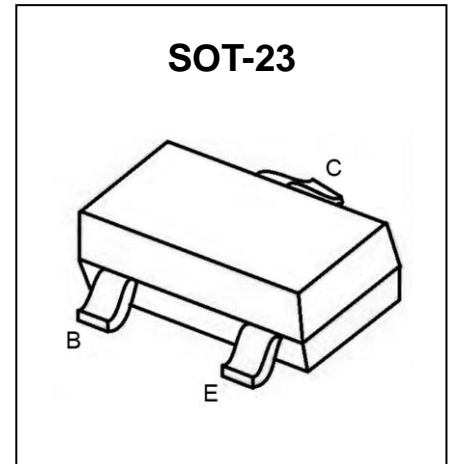




SS8050 Transistor(NPN)

Feature

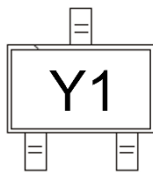
- NPN epitaxial silicon , planar design
- Collector-emitter voltage $V_{CE}=25V$
- Collector current $I_C=1.5A$
- In compliance with ER RoHS 2002/95/EC directives
- Transition frequency $f_T >100MHz@I_C=50mA$, $V_{CE}=10V_{dc}, F=30MHz$



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	1.5	A
Power Dissipation	P_d	0.3	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

MARKING:



Classification of hfe:

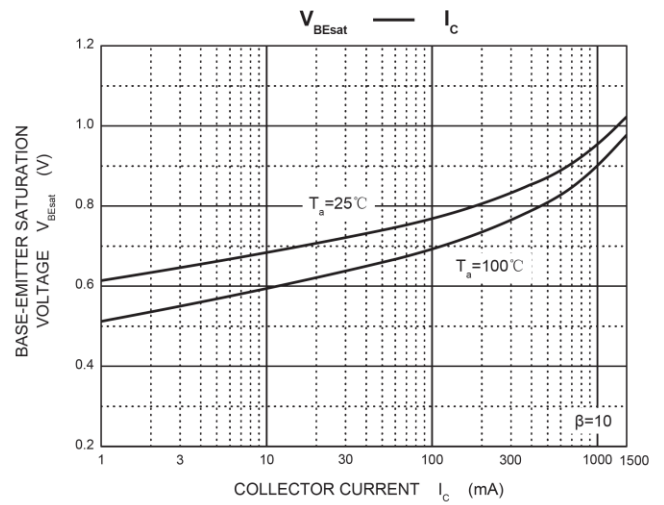
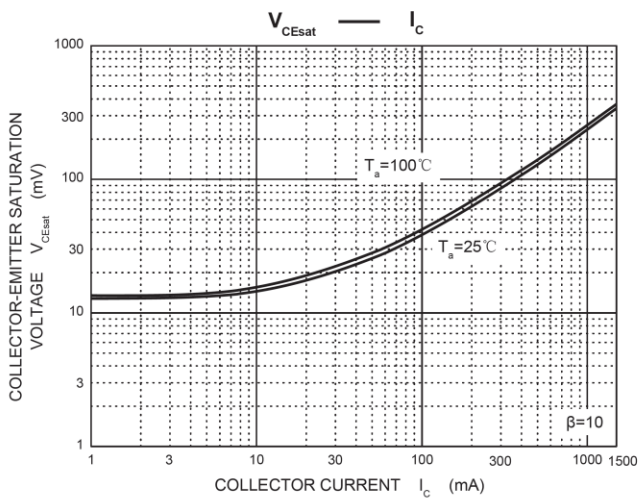
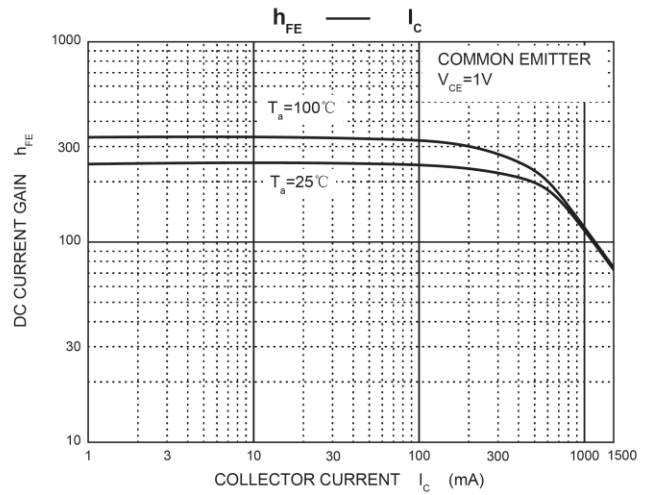
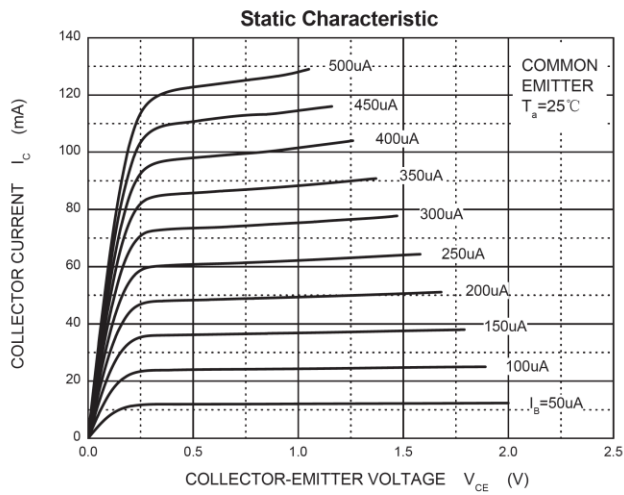
RANK	L	H	J
RANGE	120~200	200~350	350~400

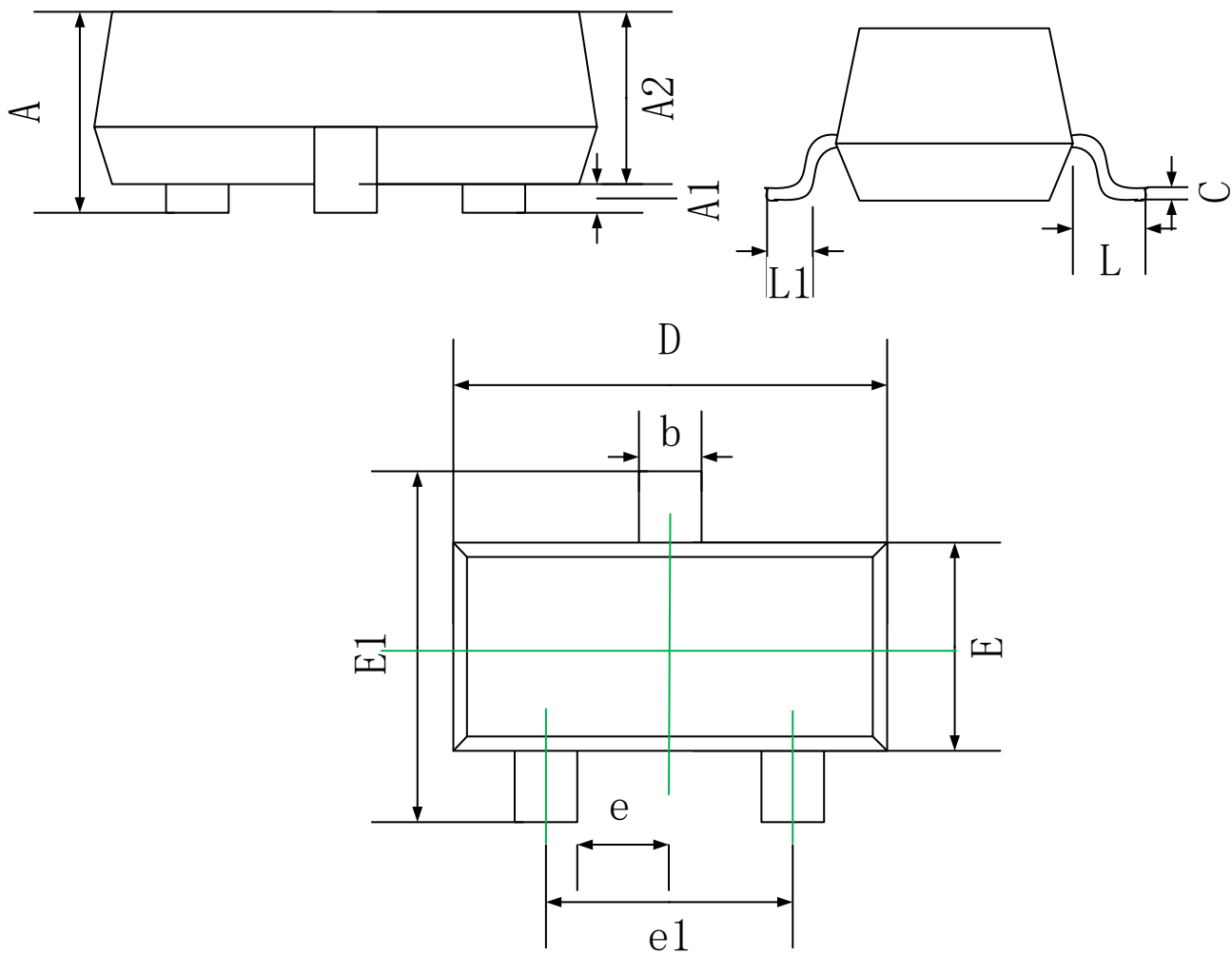
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =100μA, I _E =0	40		V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =1mA, I _B =0	25		V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E =100μA, I _C =0	5		V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0		100	nA
Collector cut-off current	I _{CEO}	V _{CE} =20V, I _B =0		100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0		100	nA
DC current gain	h _{FE}	V _{CE} =1V, I _C =0.1mA	40		
	h _{FE}	V _{CE} =1V, I _C =1mA	70		
	h _{FE}	V _{CE} =1V, I _C =100mA	100	400	
	h _{FE}	V _{CE} =1V, I _C =400mA	60		
	h _{FE}	V _{CE} =1V, I _C =800mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B =80mA		0.5	V
		I _C =500mA, I _B =50mA		0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA		1.1	V
		I _C =800mA, I _B =80mA		1.2	V
Transition frequency	f _T	V _{CE} = 10V, I _C =50mA, f=30MHz	100		MHZ
Input capacitance	C _{IB}	V _{CB} = 5V, I _E =0, f=1MHz		4	pF
Output capacitance	C _{OB}	V _{EB} = 0.5V, I _C =0, f=1MHz		8	pF
Delay time	t _d	V _{CC} =3V, V _{BE} =0.5V,		35	nS
Rise time	t _r	I _C =10mA, I _B =1mA		35	nS
Storage time	t _s	V _{CC} =3V, V _{BE} =0.5V,		200	nS
Fall time	t _f	I _{B1} = I _{B2} =-1mA		50	nS

*Pulse Test: Pulse Width<300uS , Duty Cycle<2.0%

Typical Characteristics



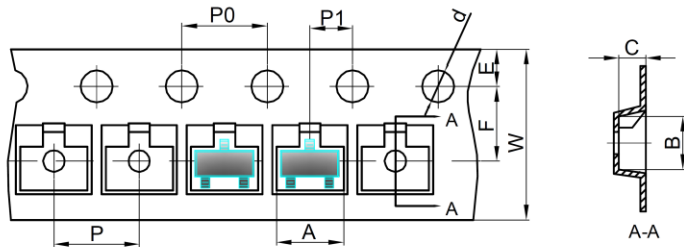
SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

SOT-23 Tape and Reel

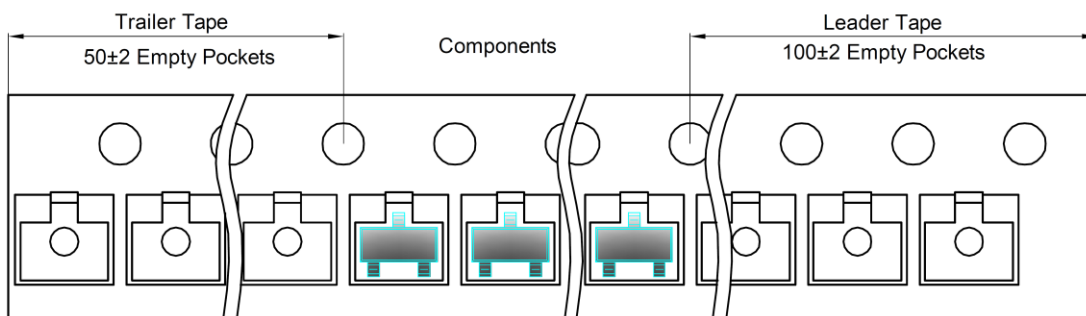
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

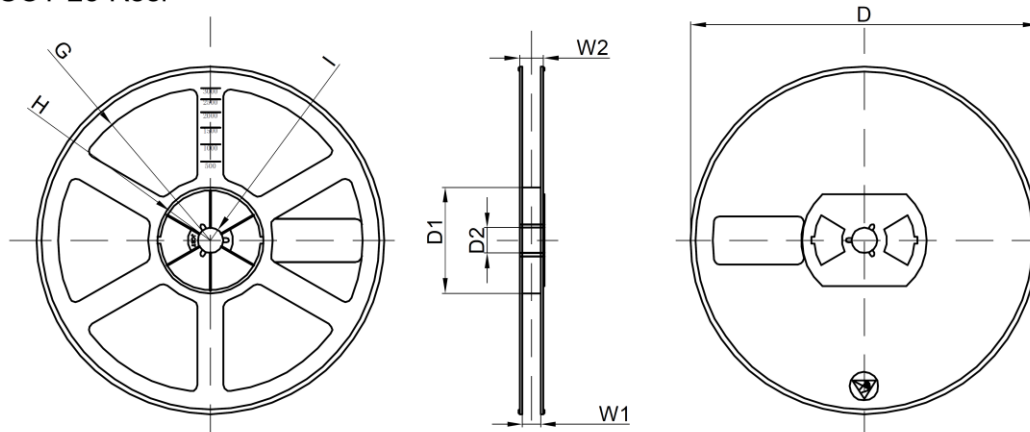


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)